

# NCE15GD120T 1200V, 15A, Trench NPT IGBT

## Features

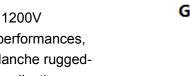
- Trench NPT( Non Punch Through) IGBT
- High speed switching
- Low saturation voltage: V<sub>CE(sat)</sub>=2.0V@I<sub>C</sub>=15A
- High input impedance

### Applications

- Inductive heating, Microwave oven, Inverter, UPS, etc.
- Soft switching applications

### **General Description**

Using advanced Trench NPT technology, NCE's 1200V IGBTs offers superior conduction and switching performances, and easy parallel operation with exceptional avalanche ruggedness. This device is designed for soft switching applications.



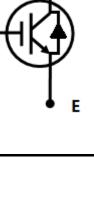
## Absolute Maximum Ratings

Symbol	Description	Ratings	Units
V <sub>CES</sub>	Collector to Emitter Voltage	1200	V
$V_{GES}$	Gate to Emitter Voltage	+/-30	V
Ι <sub>C</sub>	Continuous Collector Current @T <sub>C</sub> =25°C	30	Α
	Continuous Collector Current @T <sub>C</sub> =100°C	15	A
I <sub>CM</sub> (1)	Pulsed Collector Current	45	А
I <sub>F</sub>	Diode Continuous Forward Current @T <sub>C</sub> =100°C	15	
I <sub>FM</sub>	Diode Maximum Forward Current	90	A
P <sub>D</sub>	Maximum Power Dissipation @T <sub>C</sub> =25°C	220	W
	Maximum Power Dissipation @T <sub>c</sub> =100°C	88	W
TJ	Operating Junction Temperature	-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
	Maximum Lead Temp. for soldering Purposes, 1/8" from		
$T_L$	case for 5seconds	300	°C

#### Notes:

1. Repetitive rating, Pulse width limited by max. junction temperature







### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
R <sub>JC</sub>	Thermal Resistance, Junction to Case	-	0.57	°C/W
R <sub>JA</sub>	Thermal Resistance, Junction to Ambient	-	40	°C/W

## Electrical Characteristics of the IGBT $_{T_{c}=25^{\circ}C}$

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Char	acteristics					
$BV_{CES}$	Collector to Emitter	V <sub>GE</sub> =0V, Ic=1mA	1200	-		V
	Breakdown Voltage	V <sub>GE</sub> =0V, IC= IIIIA	1200	-	-	v
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE}$ = $V_{CES}$ , $V_{GE}$ =0V	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE}$ = $V_{GES}$ , $V_{CE}$ =0V	-	-	+/-250	nA
On Char	acteristics					
$V_{\text{GE(th)}}$	G-E Threshold Voltage	$I_C$ =15mA, $V_{CE}$ = $V_{GE}$	4.0	5.5	7.0	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation	I <sub>C</sub> =15A, V <sub>GE</sub> =15V T <sub>C</sub> =25°C	-	2	2.5	V
	Voltage	I <sub>C</sub> =15A, V <sub>GE</sub> =15V T <sub>C</sub> =125°C	-	2.15	-	V
Dynamic	Characteristics					
Cies	Input Capacitance		-	2350	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE}$ =30V, $V_{GE}$ =0V,	-	70	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	f=1MHz	-	45	-	pF
Switchin	g Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		_	33	_	ns
t <sub>r</sub>	Rise Time		_	80	_	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> =600V,I <sub>C</sub> =15A,	-	160	-	ns
t <sub>f</sub>	Fall Time	R <sub>G</sub> =10Ω,V <sub>GE</sub> =15V,	-	255	330	ns
E <sub>on</sub>	Turn-On Switching Loss	Resistive Load,	-	0.3	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss	T <sub>C</sub> =25°C	-	0.58	0.74	mJ
E <sub>ts</sub>	Total Switching Loss		-	0.88	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	30	-	ns
tr	Rise Time		-	115	-	ns
$t_{d(off)}$	Turn-Off Delay Time	V <sub>CC</sub> =600V,I <sub>C</sub> =15A,	-	170	-	ns
t <sub>f</sub>	Fall Time	$R_{G}$ =10 $\Omega$ , $V_{GE}$ =15V,	-	390	-	ns
Eon	Turn-On Switching Loss	Resistive Load,	-	0.38	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss	T <sub>C</sub> =125°C	-	0.89	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	1.27	-	mJ
Qg	Total Gate Charge		-	100	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CC</sub> =600V,I <sub>C</sub> =15A,	-	19	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	V <sub>GE</sub> =15V	-	45	-	nC



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## Electrical Characteristics of Diode $T_{c=25^{\circ}C}$

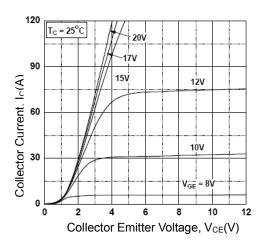
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
V <sub>FM</sub>		I <sub>F</sub> =15A	25°C		1.4	1.8	V
	Diode Forward Voltage		125°C		1.42		V
t <sub>rr</sub>	Diode Reverse Recovery		25°C		575		ns
	Time		125°C		577		ns
I <sub>rr</sub>	Diode Peak Reverse	I <sub>F</sub> =15A,	25°C		30		Α
	Recovery Current	dl/dt=200A/us	125°C		37		A
Q <sub>rr</sub>	Diode Reverse Recovery		25°C		8.7		uC
	Charge		125°C		10.7		uC



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## **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 



# Figure 3. Saturation Voltage vs. Case

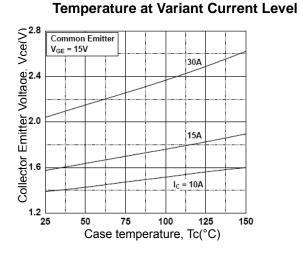


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

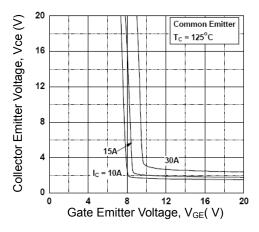


Figure 2. Typical Saturation Voltage

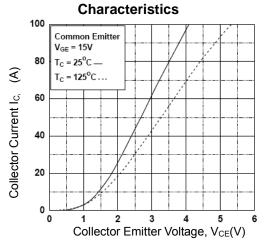


Figure 4. Saturation Voltage vs. V<sub>GE</sub>

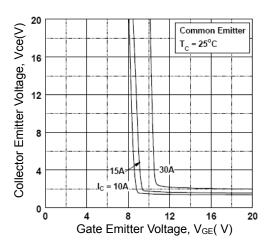
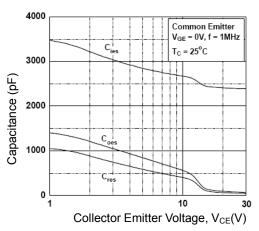


Figure 6. Capacitance Characteristics



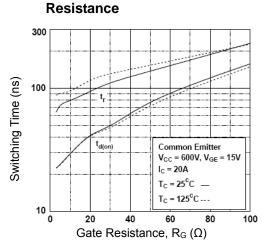




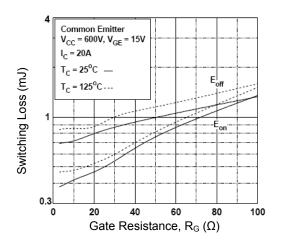
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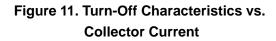
### **Typical Performance Characteristics (Continued)**

### Figure 7. Turn-on Characteristics vs. Gate









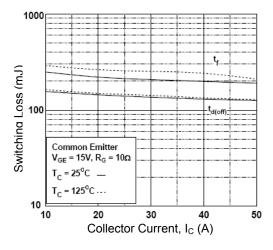


Figure 8. Turn-off Characteristics vs. Gate Resistance

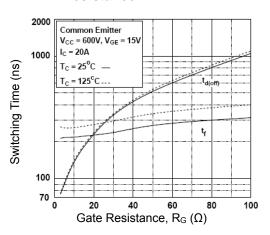
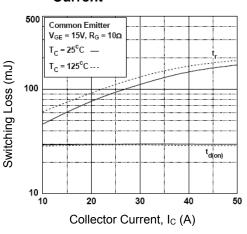
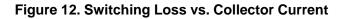
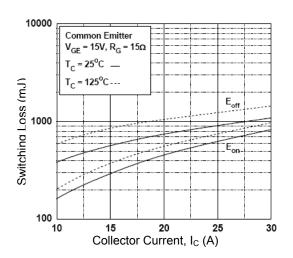


Figure 10. Turn-on Characteristics vs. Collector Current



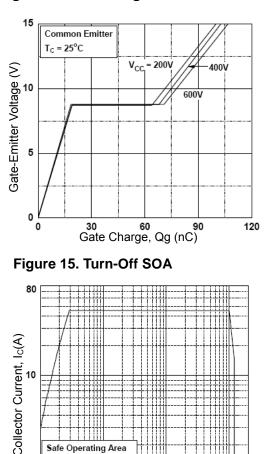






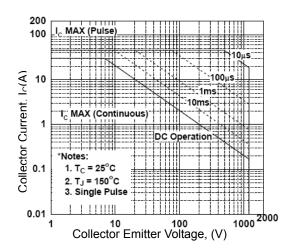
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### **Typical Performance Characteristics (Continued)**



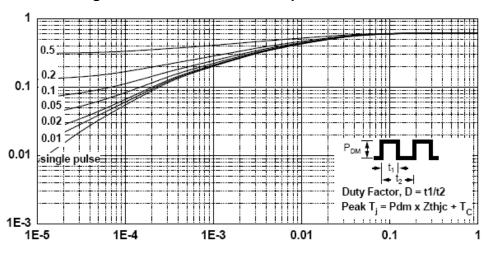
### Figure13. Gate Charge Characteristics

#### Figure 14. SOA Characteristics



#### Figure 16. Transient Thermal Impedance of IGBT

1000 2000



Safe Operating Area V<sub>GE</sub> = 15V, T<sub>C</sub> = 125°C

10

100

Collector Emitter Voltage, (V)

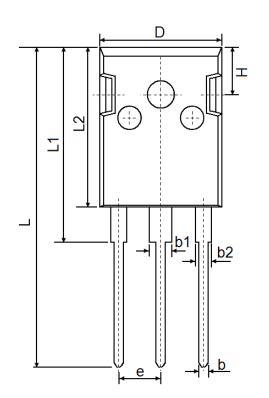
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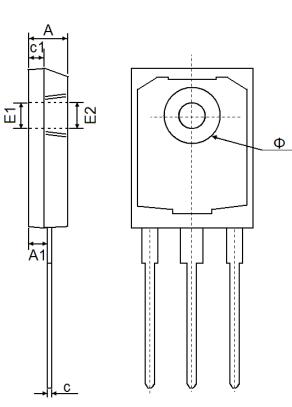




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## **TO-247 Package Information**





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.850	5.150	0.191	0.200	
A1	2.200	2.600	0.087	0.102	
b	1.000	1.400	0.039	0.055	
b1	2.800	3.200	0.110	0.126	
b2	1.800	2.200	0.071	0.087	
С	0.500	0.700	0.020	0.028	
c1	1.900	2.100	0.075	0.083	
D	15.450	15.750	0.608	0.620	
E1	3.500 REF		0.138 REF		
E2	3.600 REF		0.142 REF		
L	40.900	41.300	1.610	1.626	
L1	24.800	25.100	0.976	0.988	
L2	20.300	20.600	0.799	0.811	
Φ	7.100	7.300	0.280	0.287	
e	5.450 TYP		0.215 TYP		
Н	5.980 REF		0.235 REF		



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